

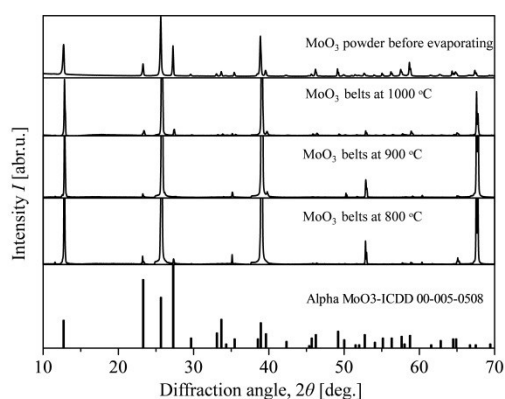
## Synthesis of MoO<sub>3</sub> belts by thermal evaporation method

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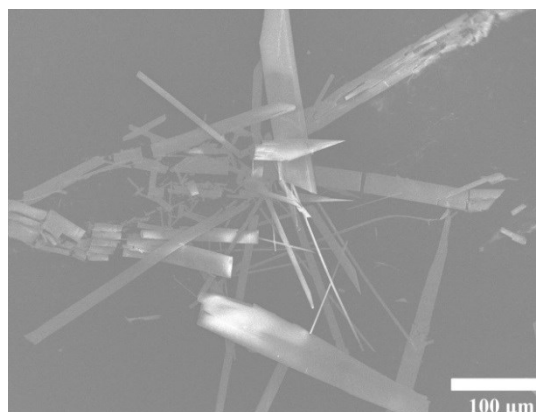
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MoO<sub>3</sub> is one of the transition metal oxides, and its one dimension structure has been recognized to be a promising material for many applications including, catalysis, electronics devices, optical-display devices, chemical synthesis, and battery applications.<sup>1,2</sup> In this presented work, a large-scale of MoO<sub>3</sub> belts was synthesized at different temperatures from 800-1050 °C by using a tube furnace. MoO<sub>3</sub> belts were deposited inside the tube, on the surface of inner tube-wall. Figure 1 shows the XRD result with the highly aligned  $\alpha$ -MoO<sub>3</sub> crystals (ICDD #000050508). The FE-SEM image of MoO<sub>3</sub> belts synthesized at 900°C is shown in Fig. 2. In comparing with previous studies,<sup>3</sup> this experiment is considered as a simple method to synthesize MoO<sub>3</sub> belts with a large amount. The belts were formed under a vapor- solid mechanism. At the first step, the MoO<sub>3</sub> at a temperature above 750°C was evaporated; by controlling the flowing gas in the furnace, the vapor moved to a lower temperature area then started deposited on the tube wall. At a fixed point on the tube, the MoO<sub>3</sub> belts were formed and collected. It is assumed that by varying the flowing gas and the temperature, the size and quantity of belts could be controlled.



**Fig. 1.** The XRD patterns of MoO<sub>3</sub> belts at different temperatures.



**Fig. 2.** The image of belts taken by FE-SEM of sample evaporated at 900 °C.

### References

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3. P. Badica: *Crystal Growth & Design*. **7** [4](2007)794.